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(54) Title: EPITAXIAL METHODS AND STRUCTURES FOR FORMING SEMICONDUCTOR MATERIALS

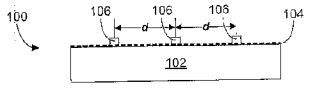


Fig. 1A

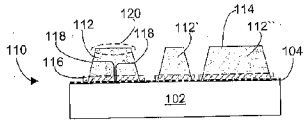


Fig. 1B

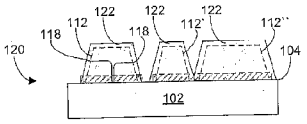


Fig. 1C

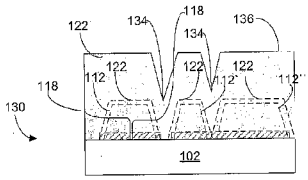


Fig. 1D

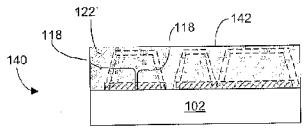


Fig. 1E

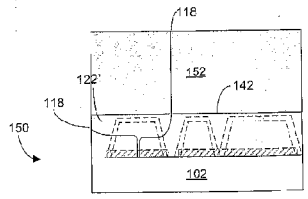


Fig. 1F

(57) Abstract: Methods and structures for producing semiconductor materials, substrates and devices with improved characteristics are disclosed. Structures and methods for forming reduced strain structures include forming a plurality of substantially strain relaxed island structures and utilizing such island structures for subsequent further growth of strain relaxed substantial continuous layers of semiconductor material.

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